

Silicon Transistor

2N5827

These silicon, planar, passivated, epitaxial transistors are intended to satisfy a broad range of general purpose signal level applications at audio and intermediate frequencies.

Features:

- Excellent Gain Linearity—particularly designed for operation in the 10 microampere to 20 milliampere range.
- 2:1 DC gain ratio per group.
- Low Collector Saturation Voltage
- Epoxy Encapsulation with Proved Reliability—excellent characteristic stability under environmental stresses, 85°C—85% RH.

absolute maximum ratings: (25°C) (unless otherwise specified)

Voltages

*Collector to Emitter	V_{CE0}	40	Volts
*Emitter to Base	V_{EB0}	5	Volts
*Collector to Base	V_{CB0}	50	Volts

Current

*Collector (continuous)	I_C	100	mA
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Dissipation

*Total Power (Free Air @ 25°C) ⁽¹⁾	P_T	360	mW
Total Power (Free Air @ 55°C)	P_T	260	mW

Temperature

*Storage	T_{ST0}	-65 to +150	°C
*Operating	T_J	-65 to +125	°C
*Lead soldering, 1/16" ± 1/32" from case for 10 secs. max.	T_L	+260	°C

⁽¹⁾Derate 3.60 mW/°C increase in ambient temperature above 25°C.

